

L Number	Hits	Search Text	DB	Time stamp
6	426666	gate	USPAT; US-PGPUB	2004/10/17 15:59
7	55159	gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))	USPAT; US-PGPUB	2004/10/17 15:59
8	54305	(gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))	USPAT; US-PGPUB	2004/10/17 15:59
9	49792	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)	USPAT; US-PGPUB	2004/10/17 16:03
10	41114	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)	USPAT; US-PGPUB	2004/10/17 16:03
11	32806	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)	USPAT; US-PGPUB	2004/10/17 16:01
12	4723	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS	USPAT; US-PGPUB	2004/10/17 16:01
13	3736	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS and PMOS	USPAT; US-PGPUB	2004/10/17 16:01
14	57	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS and PMOS and ((etch\$3 pattern\$3) with oxide with nitride with rate)	USPAT; US-PGPUB	2004/10/17 16:01
15	466501	gate	EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:59
16	12666	gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))	EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:59
17	50733	(gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon near3 oxide) SiO3 ("Si" adj3 "O.sub.3"))	USPAT; US-PGPUB	2004/10/17 16:00
18	8807	(gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon near3 oxide) SiO3 ("Si" adj3 "O.sub.3"))	EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:00
19	46144	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)	USPAT; US-PGPUB	2004/10/17 16:00
20	37139	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3"))) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4)	USPAT; US-PGPUB	2004/10/17 16:04

21	5410	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS	USPAT; US-PGPUB	2004/10/17 16:01
22	4285	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS	USPAT; US-PGPUB	2004/10/17 16:01
23	65	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate)	USPAT; US-PGPUB	2004/10/17 16:01
25	6725	(gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")) and (etch\$3 pattern\$4)	EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:03
26	2828	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)	EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:04
27	1096	((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4)	EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:05